

Davit A Ghazaryan

List of Publications by Year in descending order

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Version: 2024-02-01

13
papers

835
citations

933447

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1125743

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15
all docs

15
docs citations

15
times ranked

1824
citing authors

#	ARTICLE	IF	CITATIONS
1	Magnon-assisted tunnelling in van der Waals heterostructures based on CrBr ₃ . Nature Electronics, 2018, 1, 344-349.	26.0	239
2	Engineering Graphene Flakes for Wearable Textile Sensors <i>via</i> Highly Scalable and Ultrafast Yarn Dyeing Technique. ACS Nano, 2019, 13, 3847-3857.	14.6	179
3	Tuning the valley and chiral quantum state of Dirac electrons in van der Waals heterostructures. Science, 2016, 353, 575-579.	12.6	88
4	Phonon-Assisted Resonant Tunneling of Electrons in Grapheneâ€“Boron Nitride Transistors. Physical Review Letters, 2016, 116, 186603.	7.8	78
5	Unusual Suppression of the Superconducting Energy Gap and Critical Temperature in Atomically Thin NbSe ₂ . Nano Letters, 2018, 18, 2623-2629.	9.1	70
6	Graphene hot-electron light bulb: incandescence from hBN-encapsulated graphene in air. 2D Materials, 2018, 5, 011006.	4.4	43
7	Planar and van der Waals heterostructures for vertical tunnelling single electron transistors. Nature Communications, 2019, 10, 230.	12.8	43
8	Tunnel spectroscopy of localised electronic states in hexagonal boron nitride. Communications Physics, 2018, 1, .	5.3	33
9	High-temperature electronic devices enabled by hBN-encapsulated graphene. Applied Physics Letters, 2019, 114, .	3.3	32
10	Stacking transition in bilayer graphene caused by thermally activated rotation. 2D Materials, 2017, 4, 011013.	4.4	20
11	Twisted monolayer and bilayer graphene for vertical tunneling transistors. Applied Physics Letters, 2021, 118, .	3.3	7
12	Field-induced insulating states in a graphene superlattice. Physical Review B, 2019, 99, .	3.2	2
13	On the Role of Structural Imperfections of Graphene in Resonant Tunneling through Localized States in the h-BN Barrier of van-der-Waals Heterostructures. Semiconductors, 2020, 54, 291-296.	0.5	0